

#### NPN SILICON PLANAR SWITCHING TRANSISTORS

### 2N1481, 2N1482

TO- 39 Metal Can Package



# Medium Power Amplifier and Switching Applications

#### ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	2N1481	2N1482	UNIT
Collector Emitter Voltage	V <sub>CEO</sub>	40	55	V
Collector Emitter Voltage	V <sub>CEX</sub>	60	100	V
Collector Base Voltage	V <sub>CBO</sub>	60	100	V
Emitter Base Voltage	V <sub>EBO</sub>	6.0		V
Collector Current Continuous	I <sub>C</sub>	1.5		A
Power Dissipation at T <sub>a</sub> =25 <sup>o</sup> C	P <sub>D</sub>	1.0		W
Derate Above 25°C		5.71		mW/ °C
Power Dissipation at T <sub>c</sub> =25 <sup>o</sup> C	PD	5.0		W
Derate Above 25°C		28.6		mW/ ⁰C
Operating And Storage Junction Temperature Range	т <sub>ј</sub> , Т <sub>stg</sub>	- 65 to +200		°C

#### THERMAL RESISTANCE

Thermal Resistance Junction to Ambient	R <sub>th (j-a)</sub>	175	°C/W
Thermal Resistance Junction to Case	R <sub>th (j-c)</sub>	35	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless specified otherwise )

DESCRIPTION	SYMBOL	TEST CONDITION	2N1481	2N1482	UNIT
Collector Emitter Voltage	V <sub>CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	>40	>55	V
Collector Emitter Breakdown Voltage	V <sub>CEX</sub>	$I_{C}$ =250uA, $V_{BE}$ =1.5V	>60	>100	V
Collector Cut-Off Current	I <sub>CBO</sub>	$V_{CB}$ =30V, I <sub>E</sub> =0	<10		μA
		$V_{CB}$ =30V, I <sub>E</sub> =0, T <sub>a</sub> =150 <sup>O</sup> C	<500		μA
Emitter Cut-Off Current	I <sub>EBO</sub>	$V_{EB}=6V$ , $I_{C}=0$	<10		μA
Collector Emitter Saturation Voltage	*V <sub>CE (sat)</sub>	I <sub>C</sub> =200mA, I <sub>B</sub> =10mA	<0	.75	V
Base Emitter on Voltage	*V <sub>BE (ON)</sub>	$I_C$ =200mA, $V_{CE}$ =4V	<3	3.0	V
DC Current Gain	*h <sub>FE</sub>	$I_{C}$ =200mA, $V_{CE}$ =4V	35-	100	

#### \*Pulse Test: Pulse Width $\leq$ 300ms, Duty Cycle $\leq$ 2%

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TO- 39 Metal Can Package

#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless specified otherwise)

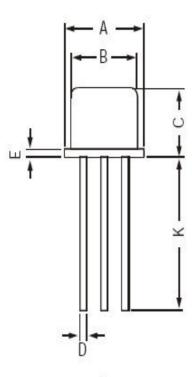
#### DYNAMIC CHARACTERISTICS

DESCRIPTION	SYMBOL	<b>TEST CONDITION</b>	2N1481 2N1482	UNIT
Small Signal Current Gain	h <sub>fe</sub>	V <sub>CE</sub> =4V, I <sub>C</sub> =5mA, f=1KHz	TYP 50	
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz	TYP 150	pF

SWITCHING TIME					
DESCRIPTION	SYMBOL	TEST CONDITION	2N1481	2N1482	UNIT
Turn-On Time	t <sub>ON</sub>		Тур 1.2		μS
Storage time	t <sub>ata</sub>	I <sub>C</sub> =200mA, R <sub>L</sub> =60Ω I <sub>B1</sub> =20mA, I <sub>B2</sub> =85mA	Тур 0.6		μs
Fall Time	t <sub>f</sub>	DI, DZ CO	Тур 1.0		μs

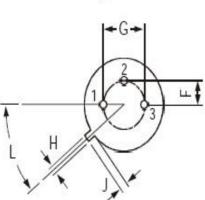
\*Pulse Test: Pulse Width < 300ms, Duty Cycle < 2%

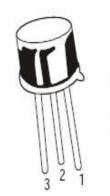
# TO- 39 Metal Can Package



# TO-39 Metal Can Package

	DIM	MIN	MAX
	Α	8.50	9.39
	В	7.74	8.50
	С	6.09	6.60
	D	0.40	0.53
F	E	—	0.88
dimensions are in mm	F	2.41	2.66
e	G	4.82	5.33
2	Н	0.71	0.86
ŝ	J	0.73	1.02
	K	12.70	2 <del></del>
M	L	42 DEG	48 DEG





PIN CONFIGURATION 1. EMITTER 2. BASE 3. COLLECTOR

# **Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	GrWt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

TO- 39 Metal Can Package

#### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

#### Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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